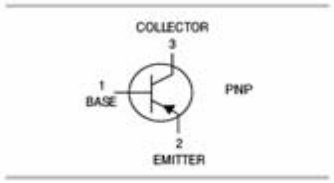
PNP Silicon Epitaxial Planar Transistor **2SA1797**

FEATURES

Lead-free

- Low $V_{CE(sat)}$=-0.35V(Max.)
  (I_C/I_B=-1A/-0.5A).
- Excellent DC current gain characteristics.
- Power dissipation P_D:0.5W.





SOT-89

APPLICATIONS

- Low frequency transistor.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1797	AGP/AGQ	SOT-89

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-55	V
V_{CEO}	Collector-Emitter Voltage	-55	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current DC Pulse	-2 -5	A
P_C	Collector Dissipation	500	mW
T_j,T_{stg}	Junction and Storage Temperature	-55~150	℃

PNP Silicon Epitaxial Planar Transistor **2SA1797**

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-50μA,I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1.0mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-50μA,I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-2V,I_C=-500mA	82		270	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1A, I_B=-50mA		-0.15	-0.35	V
Transition frequency	f_T	V_{CE}=-2V, I_E=-500mA f=100MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		36		pF

CLASSIFICATION OF h_{FE}

Rank	P	Q
Range	82-180	120-270
Marking	AGP	AGQ

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

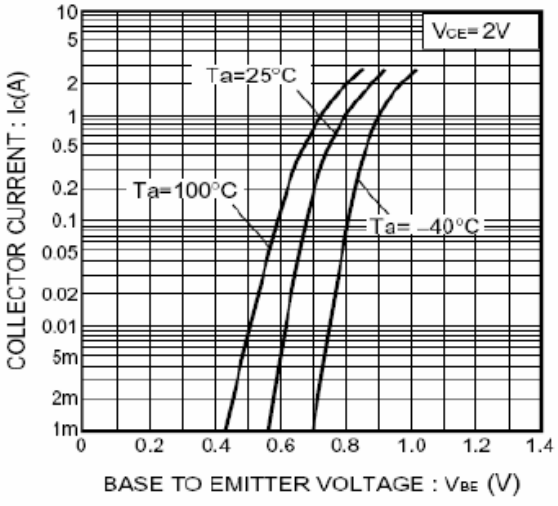


Fig.1 Grounded emitter propagation characteristics

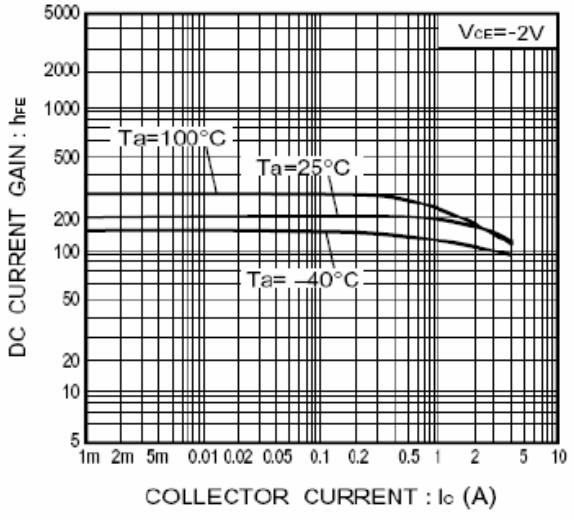


Fig.2 DC current gain vs. collector current

PNP Silicon Epitaxial Planar Transistor **2SA1797**

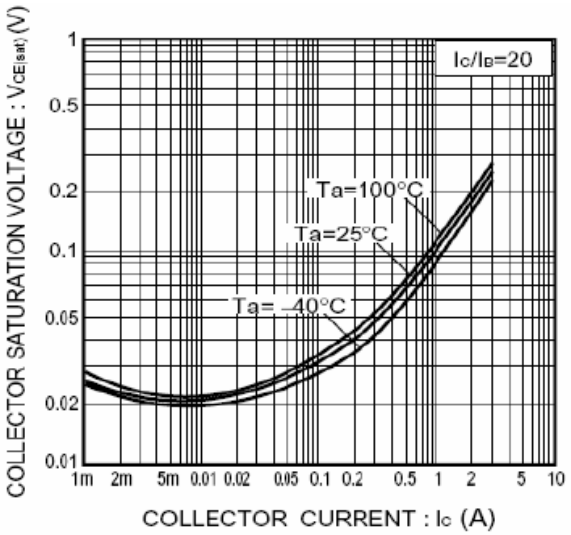


Fig.3 Collector-emitter saturation voltage vs. collector current

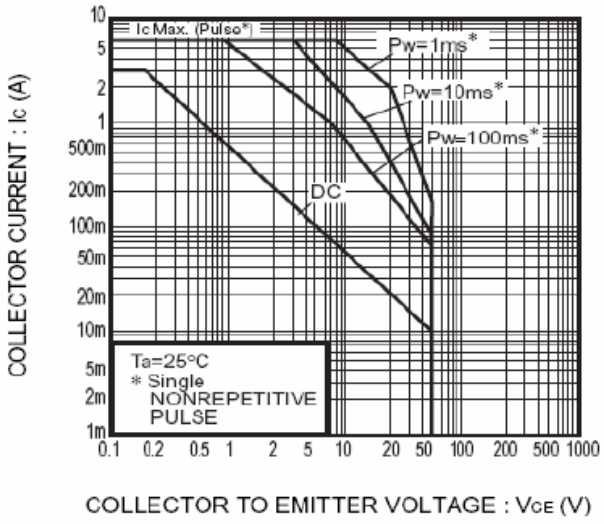
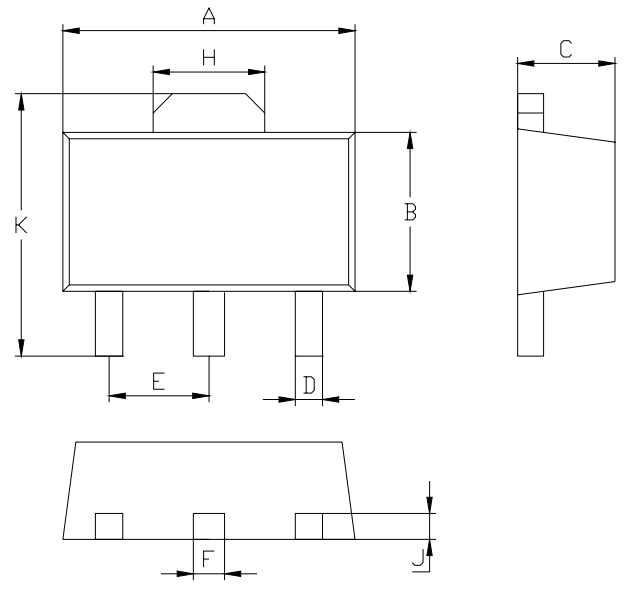


Fig.4 Safe Operating area

PACKAGE OUTLINE

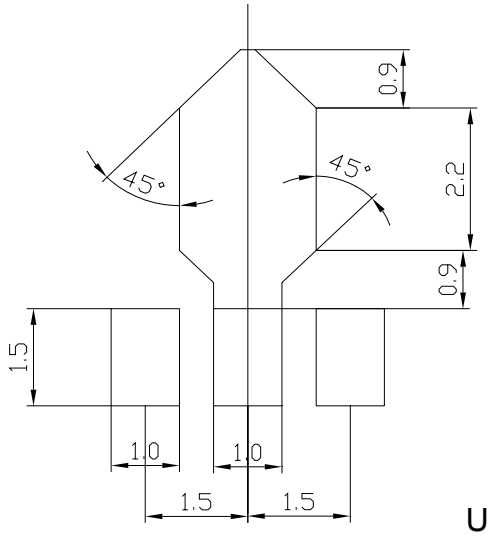
Plastic surface mounted package SOT-89



SOT-89		
Dim	Min	Max
A	4.5	4.7
B	2.3	2.7
C	1.5Typical	
D	0.35	0.55
E	1.4	1.6
F	0.4	0.6
H	1.55	1.75
J	0.4Typical	
K	4.15	4.25
All Dimensions in mm		

PNP Silicon Epitaxial Planar Transistor **2SA1797**

SOLDERING FOOTPRINT



Unit:mm

PACKAGE INFORMATION

Device	Package	Shipping
2SA1797	SOT-89	1000/Tape&Reel